SamHop Microelectronics Corp.

STS8215

Ver 3.0

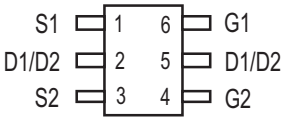
Dual N-Channel Enhancement Mode Field Effect Transistor

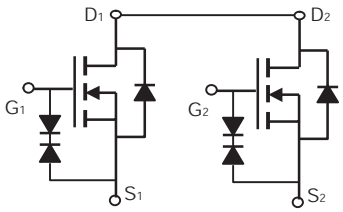
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
20V	5.5A	24.5 @ VGS=4.5V
		25.5 @ VGS=4.0V
		27.5 @ VGS=3.7V
		30.5 @ VGS=3.1V
		36.5 @ VGS=2.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- Suface Mount Package.
- ESD Protected.

TSOT 26
Top View





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		20	V
V_{GS}	Gate-Source Voltage		±12	V
I_D	Drain Current-Continuous [a]	T_A=25°C	5.5	A
		T_A=70°C	4.4	A
I_{DM}	-Pulsed [b]		22	A
P_D	Maximum Power Dissipation [a]	T_A=25°C	1.25	W
		T_A=70°C	0.8	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient [a]	100	°C/W

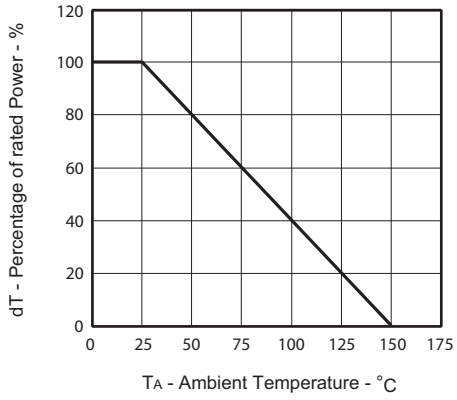
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=16V , V_{GS}=0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±12V , V_{DS}=0V			±10	uA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=1mA	0.5	0.9	1.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=4.5V , I_D=2.75A	18.5	21.5	24.5	m ohm
		V_{GS}=4.0V , I_D=2.75A	19.5	22.5	25.5	m ohm
		V_{GS}=3.7V , I_D=2.75A	20.5	23.5	27.5	m ohm
		V_{GS}=3.1V , I_D=2.75A	21.5	25.5	30.5	m ohm
		V_{GS}=2.5V , I_D=2.75A	23.5	29.5	36.5	m ohm
g_{FS}	Forward Transconductance	V_{DS}=5V , I_D=2.75A		15		S
DYNAMIC CHARACTERISTICS [c]						
C_{ISS}	Input Capacitance	V_{DS}=10V,V_{GS}=0V f=1.0MHz		485		pF
C_{OSS}	Output Capacitance			155		pF
C_{RSS}	Reverse Transfer Capacitance			135		pF
SWITCHING CHARACTERISTICS [c]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=16V I_D=2.75A V_{GS}=4.5V R_{GEN}= 6 ohm		16.5		ns
t_r	Rise Time			36		ns
$t_{D(OFF)}$	Turn-Off Delay Time			18		ns
t_f	Fall Time			39		ns
Q_g	Total Gate Charge	V_{DS}=16V,I_D=5.5A, V_{GS}=4.5V		8.6		nC
Q_{gs}	Gate-Source Charge			1.5		nC
Q_{gd}	Gate-Drain Charge			4.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=1A		0.78	1.2	V

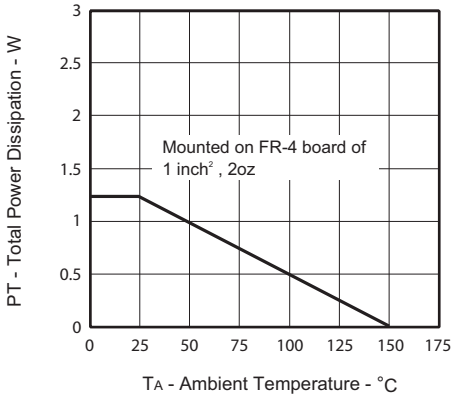
Notes

a.Surface Mounted on FR4 Board,t ≤ 10sec.
b.Pulse Test:Pulse Width ≤ 10us, Duty Cycle ≤ 1%.
c.Guaranteed by design, not subject to production testing.

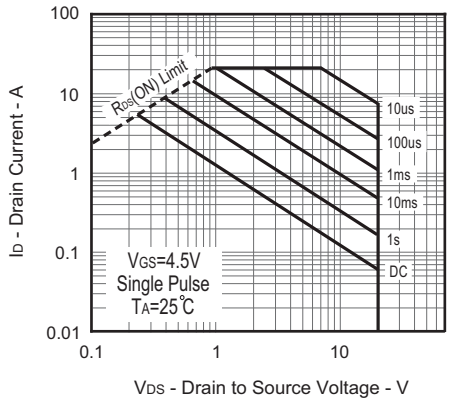
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



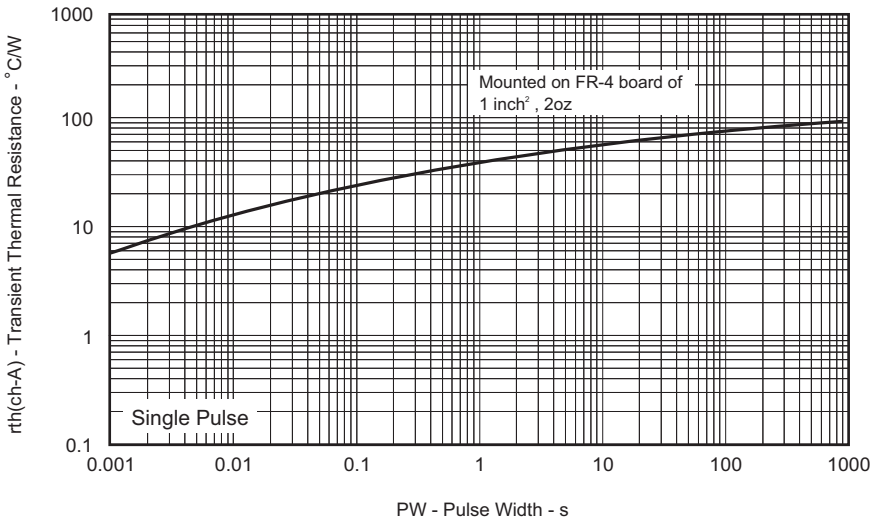
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



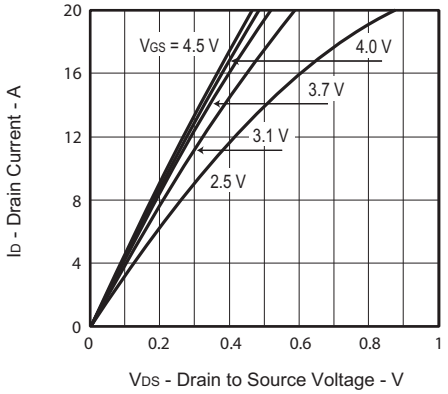
FORWARD BIAS SAFE OPERATING AREA



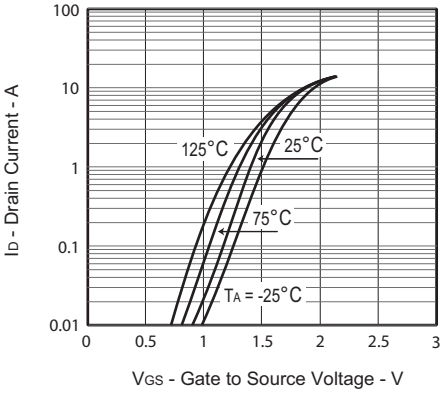
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



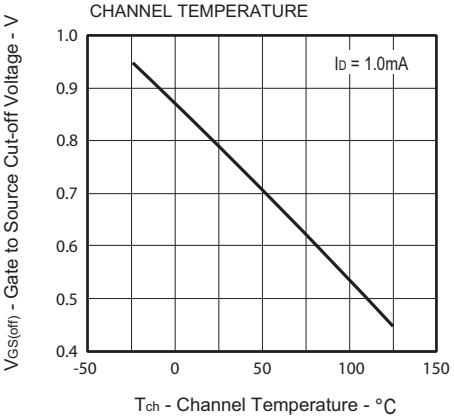
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



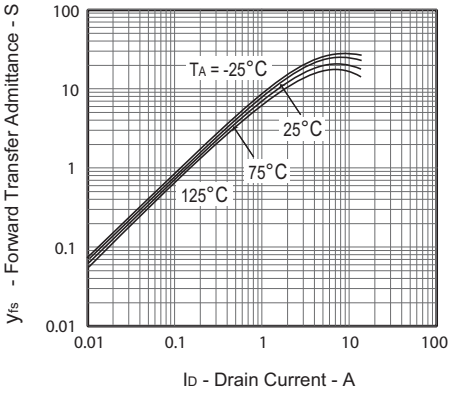
FORWARD TRANSFER CHARACTERISTICS



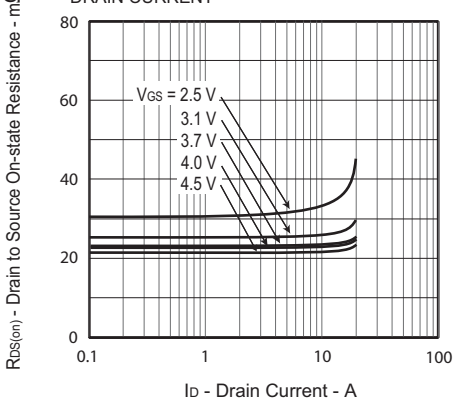
GATEBTO SOURE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



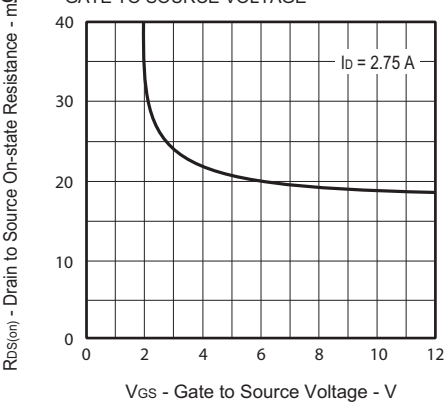
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



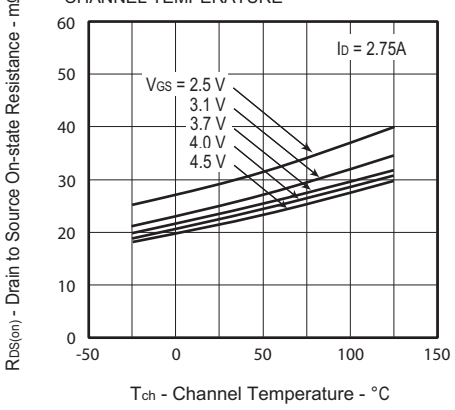
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



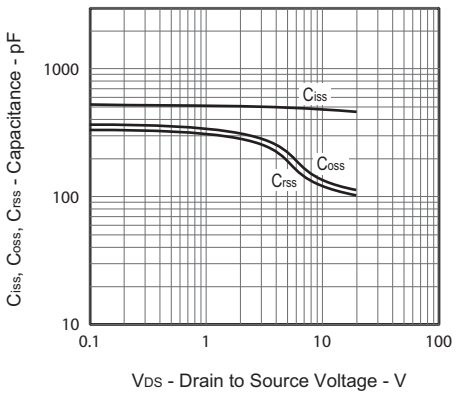
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



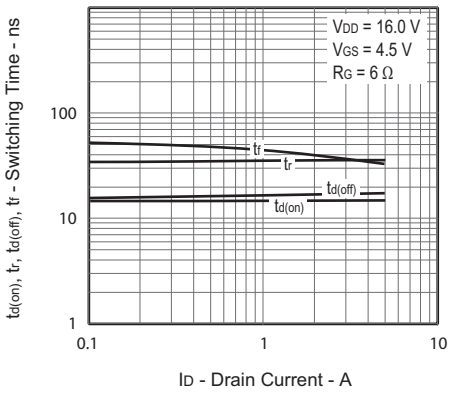
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



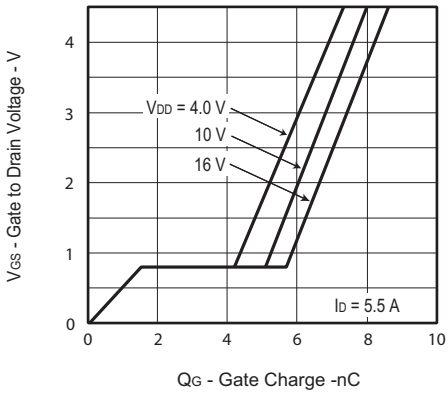
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



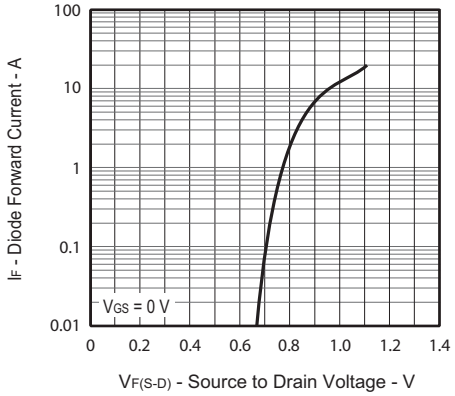
SWITCHING CHARACTERISTICS



DYNAMIC INPUT CHARACTERISTICS

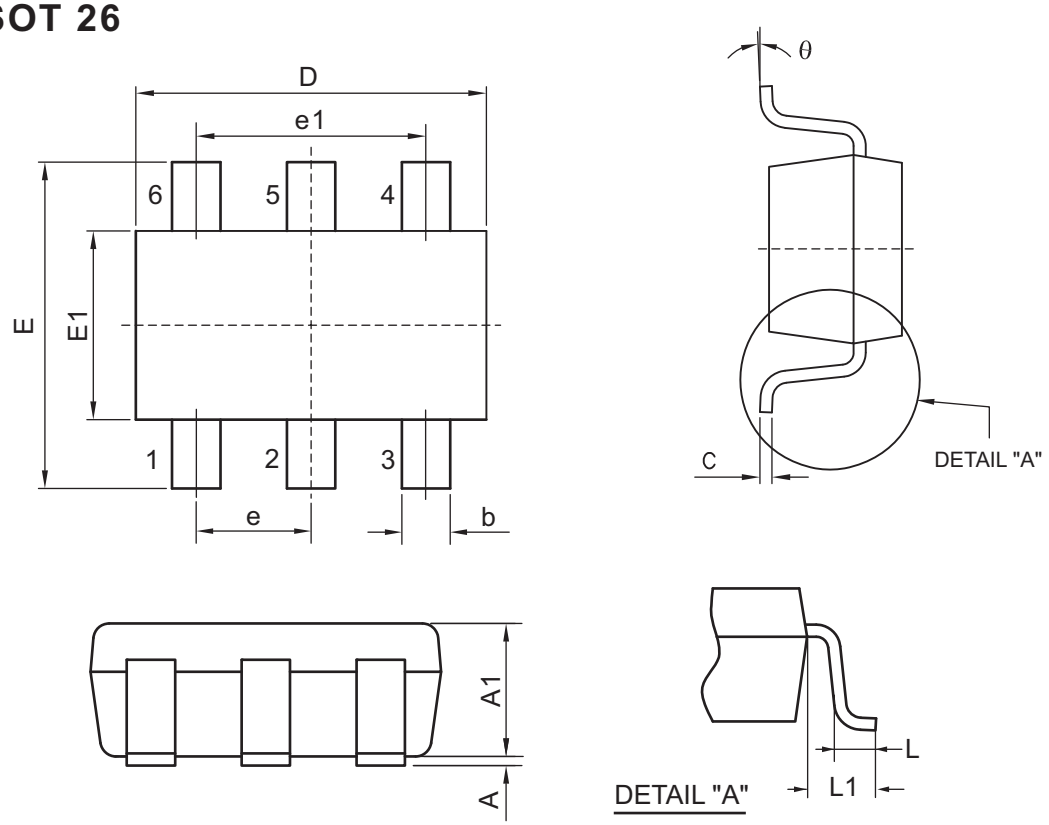


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



PACKAGE OUTLINE DIMENSIONS

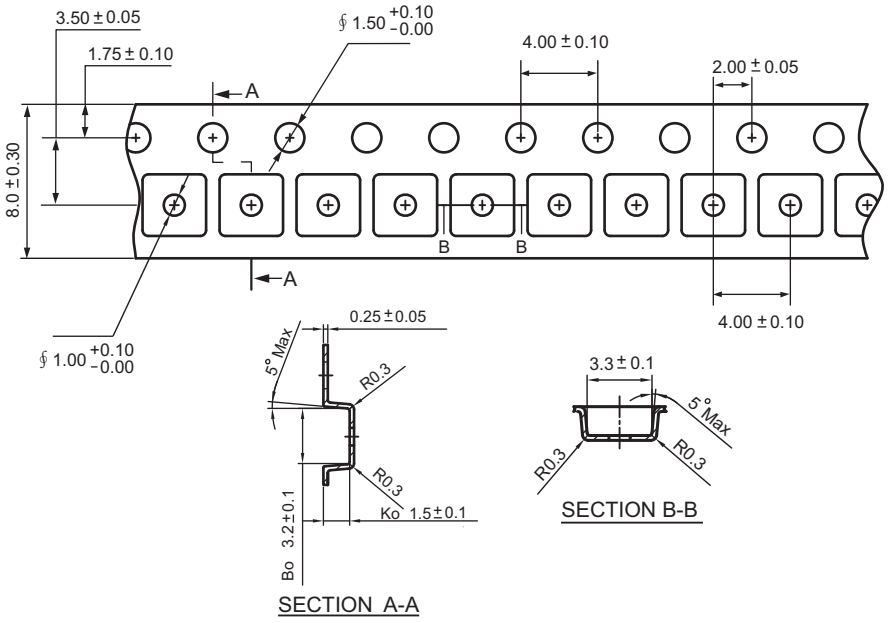
TSOT 26



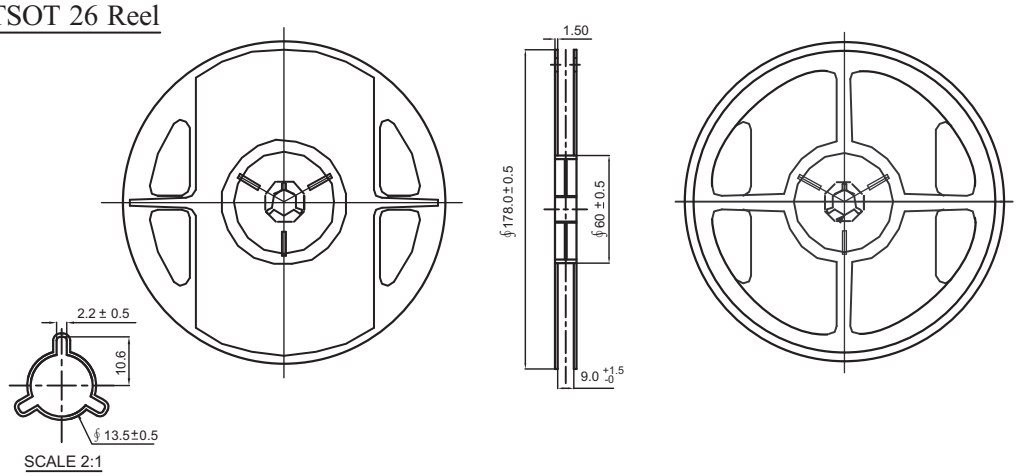
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	2.692	3.099	0.106	0.122
E	2.591	3.000	0.102	0.118
E1	1.397	1.803	0.055	0.071
e	0.950 REF.		0.037 REF.	
e1	1.900 REF.		0.075 REF.	
b	0.300	0.500	0.012	0.020
C	0.080	0.200	0.003	0.008
A	0.000	0.100	0.000	0.004
A1	0.700	0.900	0.0276	0.0354
L	0.300	0.600	0.0118	0.024
L1	0.600 REF.		0.024 REF.	
θ	0°	6°	0°	6°

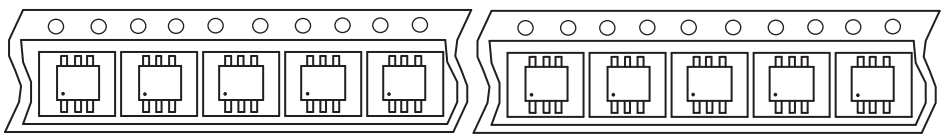
TSOT 26 Tape and Reel Data

TSOT 26 Carrier Tape



TSOT 26 Reel





SOT 26